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2811

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Attorney Docket No. FUJ 00-01013RAM
Client/Matter No. 80458.0007

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Glen Fox, Fan Chu, Brian Eastep, Tomohiro Takamatsu, Ko Nakamura, and Yoshimasa Horii

Serial No. 09/742,204

Filed: December 20, 2000

For: PROCESS FOR PRODUCING HIGH QUALITY PZT FILMS FOR FERROELECTRIC MEMORY INTEGRATED CIRCUITS

Group Art Unit: 2811

Examiner:

CERTIFICATE OF MAILING BY EXPRESS MAIL

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

- The undersigned hereby certifies that the following documents:
1. Preliminary Amendment;
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relating to the above application, were deposited as "Express Mail", Mailing Label No. EV035490605US with the United States Postal Service, addressed to The Assistant Commissioner for Patents, Washington, D.C., 20231, on 11 December 2001

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PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the above-identified patent application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 7, line 1, with the following:

A) Figure 3 is a process flowchart illustrating an alternative process wherein
the top electrode layer is deposited following a first RTA anneal, and a second
RTA anneal is performed after etching of the PZT;

Please replace the paragraph beginning at page 7, line 5, with the following:

AB Figure 4 is a process flowchart illustrating an alternative process wherein
the top electrode layer is deposited following a first RTA anneal, and a second
RTA anneal is performed after etching of the PZT and deposition of an
encapsulation layer; and